

Dual Wide Bandwidth Operational Amplifiers

The MC4558AC, C combine all the outstanding features of the MC1458 and, in addition offer three times the unity gain bandwidth of the industry standard.

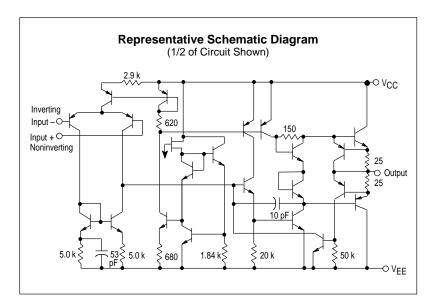
- 2.5 MHz Unity Gain Bandwidth Guaranteed (MC4558AC)
- 2.0 MHz Unity Gain Bandwidth Guaranteed (MC4558C)
- Internally Compensated
- Short Circuit Protection
- Gain and Phase Match between Amplifiers
- Low Power Consumption

MAXIMUM RATINGS ($T_A = +25^{\circ}C$, unless otherwise noted.)

Rating	Symbol	MC4558AC	MC4558C	Unit
Power Supply Voltage	V _{CC}	+22 +18 -22 -18		Vdc
Input Differential Voltage	V _{ID}	±30		V
Input Common Mode Voltage (Note 1)	VICM	±15		V
Output Short Circuit Duration (Note 2)	tsc	Continuous		
Ambient Temperature Range	TA	0 to +70		°C
Storage Temperature Range	T _{stg}	-55 to +125		°C
Junction Temperature	TJ	150		°C

NOTES: 1. For supply voltages less than ± 15 V, the absolute maximum input voltage is equal to the supply voltage.

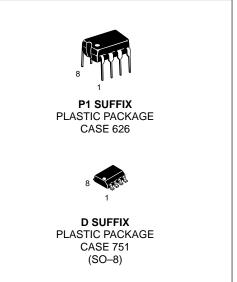
2. Short circuit may be to ground or either supply.

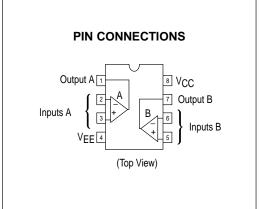


MC4558AC MC4558C

DUAL WIDE BANDWIDTH OPERATIONAL AMPLIFIERS

SEMICONDUCTOR TECHNICAL DATA





ORDERING INFORMATION

Device	Operating Temperature Range	Package
MC4558CD	$T_{\Delta} = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	SO-8
MC4558ACP1,CP1	1A = 0 10 +70 C	Plastic DIP

FREQUENCY CHARACTERISTICS ($V_{CC} = +15 \text{ V}, V_{EE} = -15 \text{ V}, T_A = 25^{\circ}\text{C}$)

2		MC4558AC		MC4558C				
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Unity Gain Bandwidth	BW	2.5	2.8	-	2.0	2.8	_	MHz
ELECTRICAL CHARACTERISTICS (V _{CC} = 15 V, V _{EE} = -15	V, T _A = 25°C	C, unless	otherwis	se noted.)			
Input Offset Voltage (R _S ≤ 10 kΩ)	VIO	-	1.0	5.0	-	2.0	6.0	mV
Input Offset Current	ΙO	-	20	200	-	20	200	nA
Input Bias Current (Note 1)	l _{IB}	-	80	500	-	80	500	nA
Input Resistance	rį	0.3	2.0	-	0.3	2.0	-	ΜΩ
Input Capacitance	C _i	-	1.4	-	-	1.4	_	pF
Common Mode Input Voltage Range	VICR	±12	±13	-	±12	±13	-	V
Large Signal Voltage Gain ($V_O = \pm 10 \text{ V}, R_L = 2.0 \text{ k}\Omega$)	AVOL	50	200	-	20	200	-	V/mV
Output Resistance	r _o	-	75	-	-	75	_	Ω
Common Mode Rejection (R _S \leq 10 k Ω)	CMR	70	90	-	70	90	_	dB
Supply Voltage Rejection Ratio (R _S \leq 10 k Ω)	PSRR	-	30	150	-	30	150	μV/V
Output Voltage Swing	٧o							V
$ \begin{array}{l} (R_L \geq 10 \; k\Omega) \\ (R_L \geq 2.0 \; k\Omega) \end{array} $		±12 ±10	±14 ±13	_	±12 ±10	±14 ±13	- -	
Output Short Circuit Current	I _{SC}	10	20	40	10	20	40	mA
Supply Currents (Both Amplifiers)	ID	_	2.3	5.0	_	2.3	5.6	mA
Power Consumption (Both Amplifiers)	PC	_	70	150	_	70	170	mW
Transient Response (Unity Gain)			''	100		- 70	170	11100
$(V_{\parallel} = 20 \text{ mV}, R_{\perp} \ge 2.0 \text{ k}\Omega, C_{\perp} \le 100 \text{ pF})$ Rise Time	tTLH	_	0.3	_	_	0.3	_	μs
$(V_I = 20 \text{ mV}, R_L \ge 2.0 \text{ k}\Omega, C_L \le 100 \text{ pF}) \text{ Overshoot}$	os	-	15	_	-	15	-	%
$(V_I = 10 \text{ V}, R_L \ge 2.0 \text{ k}\Omega, C_L \le 100 \text{ pF})$ Slew Rate	SR	1.5	1.6	_	1.0	1.6	_	V/μs
ELECTRICAL CHARACTERISTICS (V _{CC} = +15 V, V _{EE} = -15		Ĭ						., 1
Input Offset Voltage (R _S ≤ 10 kΩ)	VIO	_	1.0	6.0	_	-	7.5	mV
Input Offset Current (TA = Thigh)	IO	_	7.0	200	_	_	_	nA
$(T_A - T_{low})$		_	85	500	_	_	_	
$(T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C})$		-	_	-	-	-	300	
Input Bias Current	lв							nA
(TA = Thigh)		_	30 300	500 1500	_	_	_	
$(I_A = I_{IOW})$ $(T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C})$		_	_	-	_	_	800	
Common Mode Input Voltage Range	VICR	±12	±13	-	-	-	_	V
Large Signal Voltage Gain ($V_O = \pm 10 \text{ V}$, $R_L = 2.0 \text{ k}\Omega$)	AVOL	25	_	-	15	-	_	V/mV
Common Mode Rejection (R _S ≤ 10 kΩ)	CMR	70	90	-	-	-	_	dB
Supply Voltage Rejection Ratio (R _S \leq 10 k Ω)	PSRR	_	30	150	_	_	_	μV/V
Output Voltage Swing	٧o							V
$(R_L \ge 10 \text{ k}\Omega)$		±12	±14	-	±12	±14	_	
$(R_L \ge 2.0 \text{ k}\Omega)$		±10	±13	-	±10	±13	_	
Supply Currents (Both Amplifiers) (TA = Thigh)	ΙD	_	_	4.5	_	_	5.0	mA
$(T_A - T_{IOW})$		-	_	6.0	-	-	6.7	
Power Consumption (Both Amplifiers)	PC							mW
$(T_A = T_{high})$		_	_	135	-	_	150	
$(T_A = T_{IOW})$		_	_	180	-	-	200	

NOTES: 1. I_{IB} is out of the amplifier due to PNP input transistors. 2. T_{high} = +70°C, T_{low} = 0°C.

Figure 1. Burst Noise versus Source Resistance

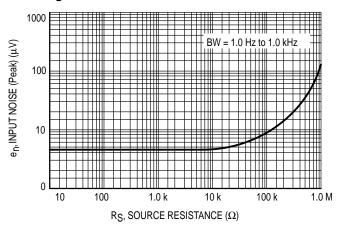


Figure 2. RMS Noise versus Source Resistance

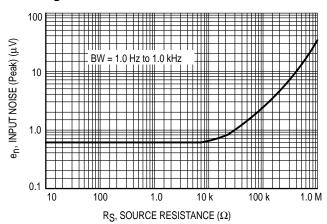


Figure 3. Output Noise versus Source Resistance

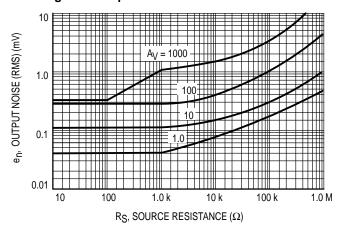


Figure 4. Spectral Noise Density

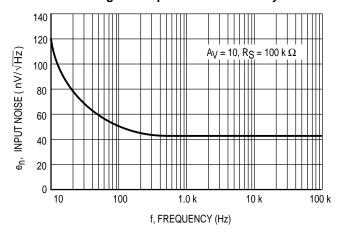
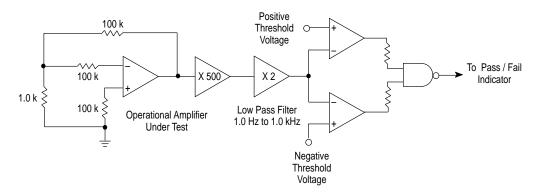


Figure 5. Burst Noise Test Circuit



Unlike conventional peak reading or RMS meters, this system was especially designed to provide the quick response time essential to burst (popcorn) noise testing.

The test time employed is 10 sec and the 20 μ V peak limit refers to the operational amplifier input thus eliminating errors in the closed loop gain factor of the operational amplifier.

Figure 6. Open Loop Frequency Response

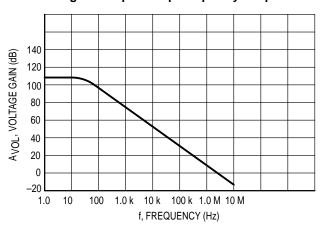


Figure 7. Phase Margin versus Frequency

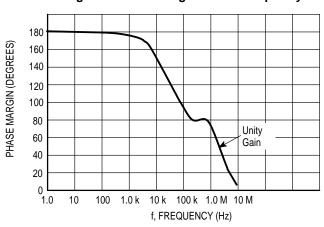


Figure 8. Positive Output Voltage Swing versus Load Resistance

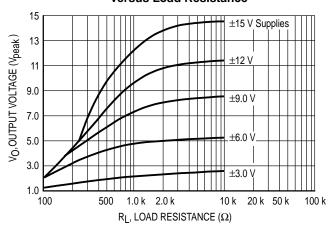


Figure 9. Negative Output Voltage Swing versus Load Resistance

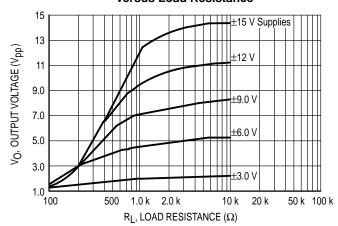


Figure 10. Power Bandwidth (Large Signal Swing versus Frequency)

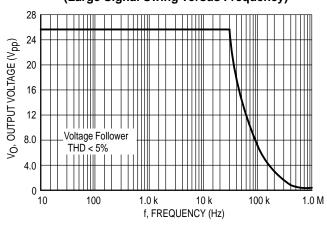
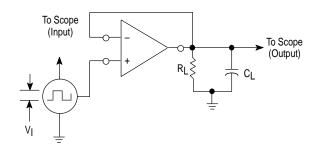
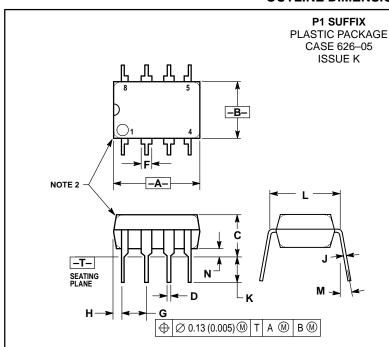


Figure 11. Transient Response Test Circuit



OUTLINE DIMENSIONS



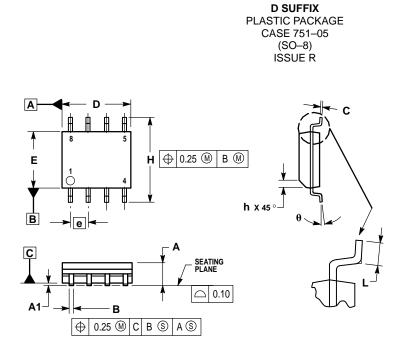
NOTES:

- DIMENSION L TO CENTER OF LEAD WHEN
- FORMED PARALLEL.

 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).

 3. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.

	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	9.40	10.16	0.370	0.400		
В	6.10	6.60	0.240	0.260		
С	3.94	4.45	0.155	0.175		
D	0.38	0.51	0.015	0.020		
F	1.02	1.78	0.040	0.070		
G	2.54	2.54 BSC		0.100 BSC		
Н	0.76	1.27	0.030	0.050		
J	0.20	0.30	0.008	0.012		
K	2.92	3.43	0.115	0.135		
L	7.62 BSC		0.300 BSC			
M		10°		10°		
N	0.76	1.01	0.030	0.040		



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 2. DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE MOLD
- PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS
 OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
С	0.18	0.25		
D	4.80	5.00		
Е	3.80	4.00		
е	1.27	1.27 BSC		
Н	5.80	6.20		
h	0.25	0.50		
L	0.40	1.25		
θ	0 0	7 °		

MC4558AC MC4558C NOTES

MC4558AC MC4558C NOTES

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